AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A method of manufacturing an electro-optical device, said method comprising the steps of:

forming a plurality of TFTs over a substrate;

forming a plurality of pixel electrodes each being connected to one of the plurality of TFTs; and

forming an EL layer over the plurality of pixel electrodes,

wherein the EL layer is formed by an ink-jet method, [[and]]

wherein the EL layer is continuous over the plurality of pixel electrodes,

wherein the electro-optical device includes a plurality of pixels,

wherein each of the plurality of pixels includes pixel electrodes adjacent each other, and

wherein a gap between one pixel and an adjacent pixel thereof is in a range of 5 to 10 times of a thickness of the EL layer.

2. (Currently Amended) A method of manufacturing an electro-optical device, said method comprising the steps of:

forming a plurality of TFTs over a substrate;

forming a plurality of pixel electrodes each being connected to one of the plurality of TFTs; and

forming an EL layer over the plurality of pixel electrodes,

wherein the EL layer is formed by an ink-jet method, [[and]]

wherein the EL layer has an oblong shape or a rectangular shape corresponding to each of the plurality of pixel electrodes,

wherein the electro-optical device includes a plurality of pixels,

wherein each of the plurality of pixels includes pixel electrodes adjacent each other, and

wherein a gap between one pixel and an adjacent pixel thereof is in a range of 5 to 10 times of a thickness of the EL layer.

3. (Currently Amended) A method of manufacturing an electro-optical device, said method comprising the steps of:

forming a plurality of TFTs over a substrate;

forming a plurality of pixel electrodes each being connected to one of the plurality of TFTs;

forming first EL layers for emitting a red color light over first pixel electrodes in the plurality of pixel electrodes;

forming second EL layers for emitting a green color light over second pixel electrodes in the plurality of pixel electrodes; and

forming third EL layers for emitting a blue color light over third pixel electrodes in the plurality of pixel electrodes,

wherein the first, second and third EL layers are formed by an ink-jet method, [[and]]

wherein the first, second and third EL layers are continuous over the plurality of pixel electrodes,

wherein the electro-optical device includes a plurality of pixels,

wherein each of the plurality of pixels includes pixel electrodes adjacent each other, and

wherein a gap between one pixel and an adjacent pixel thereof is in a range of 5 to 10 times of a thickness of each of the first, second and third EL layers.

4. (Currently Amended) A method of manufacturing an electro-optical device, said method comprising the steps of:

forming a plurality of TFTs over a substrate;

forming a plurality of pixel electrodes each being connected to one of the plurality of TFTs;

forming first EL layers for emitting a red color light over first pixel electrodes in the plurality of pixel electrodes;

forming second EL layers for emitting a green color light over second pixel electrodes in the plurality of pixel electrodes; and

forming third EL layers for emitting a blue color light over third pixel electrodes in the plurality of pixel electrodes,

wherein the first, second and third EL layers are formed by an ink-jet method, [[and]]

wherein each of the first, second and third EL layers has an oblong shape or a rectangular shape corresponding to each of the plurality of pixel electrodes,

wherein the electro-optical device includes a plurality of pixels,

wherein each of the plurality of pixels includes pixel electrodes adjacent each other, and

wherein a gap between one pixel and an adjacent pixel thereof is in a range of 5 to 10 times of a thickness of each of the first, second and third EL layers.

5. (Currently Amended) A method of manufacturing an electro-optical device, said method comprising the steps of:

forming a plurality of TFTs over a substrate;

forming an insulating layer covering the plurality of TFTs;

forming a plurality of pixel electrodes each being connected to one of the plurality of TFTs; and

forming an EL layer over the plurality of pixel electrodes,

wherein the EL layer is formed by an ink-jet method,

wherein the EL layer is continuous over the plurality of pixel electrodes, [[and]]

wherein an insulating film for preventing transmission of alkali metals is formed in a top layer of the insulating layer,

wherein the electro-optical device includes a plurality of pixels,

wherein each of the plurality of pixels includes pixel electrodes adjacent each other, and

wherein a gap between one pixel and an adjacent pixel thereof is in a range of 5 to 10 times of a thickness of the EL layer..

6. (Currently Amended) A method of manufacturing an electro-optical device, said method comprising the steps of:

forming a plurality of TFTs over a substrate;

forming an insulating layer covering the plurality of TFTs;

forming a plurality of pixel electrodes each being connected to one of the plurality of TFTs; and

forming an EL layer on the plurality of pixel electrodes,

wherein the EL layer is formed by an ink-jet method, [[and]]

wherein the EL layer has an oblong shape or a rectangular shape corresponding to each of the plurality of pixel electrodes, [[and]]

wherein an insulating film for preventing transmission of alkali metals is formed in a top layer of the insulating layer,

wherein the electro-optical device includes a plurality of pixels,

wherein each of the plurality of pixels includes pixel electrodes adjacent each other, and

wherein a gap between one pixel and an adjacent pixel thereof is in a range of 5 to 10 times of a thickness of the EL layer.

7. (Currently Amended) A method of manufacturing an electro-optical device, said method comprising the steps of:

forming a plurality of TFTs over a substrate;

forming an insulating layer covering the plurality of TFTs;

forming a plurality of pixel electrodes each being connected to one of the plurality of TFTs;

forming first EL layers for emitting a red color light over first pixel electrodes in the plurality of pixel electrodes;

forming second EL layers for emitting a green color light over second pixel electrodes in the plurality of pixel electrodes; and

forming third EL layers for emitting a blue color light over third pixel electrodes in the plurality of pixel electrodes,

wherein the first, second and third EL layers are formed by an ink-jet method,

wherein the first, second and third EL layers are continuous over the plurality of pixel electrodes, [[and]]

wherein an insulating film for preventing transmission of alkali metals is formed in a top layer of the insulating layer,

wherein the electro-optical device includes a plurality of pixels,

wherein each of the plurality of pixels includes pixel electrodes adjacent each other, and

wherein a gap between one pixel and an adjacent pixel thereof is in a range of 5 to 10 times of a thickness of each of the first, second and third EL layers.

8. (Currently Amended) A method of manufacturing an electro-optical device, said method comprising the steps of:

forming a plurality of TFTs over a substrate;

forming an insulating layer covering the plurality of TFTs;

forming a plurality of pixel electrodes each being connected to one of the plurality of TFTs;

forming first EL layers for emitting a red color light over first pixel electrodes in the plurality of pixel electrodes;

forming second EL layers for emitting a green color light over second pixel electrodes in the plurality of pixel electrodes; and

forming third EL layers for emitting a blue color light over third pixel electrodes in the plurality of pixel electrodes,

wherein the first, second and third EL layers are formed by an ink-jet method, [[and]]

wherein each of the first, second and third EL layers has have an oblong shape or a rectangular shape corresponding to each of the plurality of pixel electrodes, [[and]]

wherein an insulating film for preventing transmission of alkali metals is formed in a top layer of the insulating layer,

wherein the electro-optical device includes a plurality of pixels,

wherein each of the plurality of pixels includes pixel electrodes adjacent each other, and

wherein a gap between one pixel and an adjacent pixel thereof is in a range of 5 to 10 times of a thickness of each of the first, second and third EL layers.

9. (Canceled)

10. (Original) A method according to claim 9, wherein the gap is in a range of 250-2500 nm.

11. (Original) A method of according to claim 1, wherein the EL layer comprises an organic material.

12. (Original) A method of according to claim 1, wherein the ink jet method uses a piezo element.

13. (Original) A method according to claim 5, wherein the insulating layer comprises the insulating film for preventing transmission of alkali metals on an insulating film including an organic resin material.

14. (Original) A method according to claim 5, wherein the insulating film for preventing transmission of alkali metals comprises at least one element selected from the group consisting of B (boron), C (carbon), and N (nitrogen), Al (aluminum), Si (silicon), and P (phosphorous).

15. (Currently Amended) A method according to claim 5, wherein the insulating film for preventing transmission of alkali metals comprises Si, Al, N, O, and M,

wherein M ~~denotes at least one rare earth element, preferably at least one~~ is at least one element selected from the group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), La (lanthanum), Gd (gadolinium), Dy (dysprosium), and Nd (neodymium).

16. – 59. (Canceled)

60. (Canceled)

61. (Currently Amended) A method according to claim 2 ~~60~~, wherein the gap is in a range of 250-2500 nm.

62. (Original) A method of according to claim 2, wherein the EL layer comprises an organic material.

63. (Original) A method of according to claim 2, wherein the ink jet method uses a piezo element.

64. (Canceled)

65. (Currently Amended) A method according to claim 3 ~~64~~, wherein the gap is in a range of 250-2500 nm.

66. (Original) A method of according to claim 3, wherein each of the first, second and third EL layers comprises an organic material.

67. (Original) A method of according to claim 3, wherein the ink jet method uses a piezo element.

68. (Canceled)

69. (Currently Amended) A method according to claim 4 ~~68~~, wherein the gap is in a range of 250-2500 nm.

70. (Original) A method of according to claim 4, wherein each of the first, second and third EL layers comprises an organic material.

71. (Original) A method of according to claim 4, wherein the ink jet method uses a piezo element.

72. (Canceled)

73. (Currently Amended) A method according to claim 5 ~~72~~, wherein the gap is in a range of 250-2500 nm.

74. (Original) A method of according to claim 5, wherein the EL layer comprises an organic material.

75. (Original) A method of according to claim 5, wherein the ink jet method uses a piezo element.

76. (Canceled)

77. (Currently Amended) A method according to claim 6 ~~76~~, wherein the gap is in a range of 250-2500 nm.

78. (Original) A method of according to claim 6, wherein the EL layer comprises an organic material.

79. (Original) A method of according to claim 6, wherein the ink jet method uses a piezo element.

80. (Original) A method according to claim 6, wherein the insulating layer comprises the insulating film for preventing transmission of alkali metals on an insulating film including an organic resin material.

81. (Original) A method according to claim 6, wherein the insulating film for preventing transmission of alkali metals comprises at least one element selected from the group consisting of B (boron), C (carbon), and N (nitrogen), Al (aluminum), Si (silicon), and P (phosphorous).

82. (Currently Amended) A method according to claim 6, wherein the insulating film for preventing transmission of alkali metals comprises Si, Al, N, O, and M,

wherein M ~~denotes at least one rare earth element, preferably at least one~~ is at least one element selected from the group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), La (lanthanum), Gd (gadolinium), Dy (dysprosium), and Nd (neodymium).

83. (Canceled)

84. (Currently Amended) A method according to claim 7 ~~83~~, wherein the gap is in a range of 250-2500 nm.

85. (Original) A method of according to claim 7, wherein each of the first, second and third EL layers comprises an organic material.

86. (Original) A method of according to claim 7, wherein the ink jet method uses a piezo element.

87. (Original) A method according to claim 7, wherein the insulating layer comprises the insulating film for preventing transmission of alkali metals on an insulating film including an organic resin material.

88. (Original) A method according to claim 7, wherein the insulating film for preventing transmission of alkali metals comprises at least one element selected from the group consisting of B (boron), C (carbon), and N (nitrogen), Al (aluminum), Si (silicon), and P (phosphorous).

89. (Currently Amended) A method according to claim 7, wherein the insulating film for preventing transmission of alkali metals comprises Si, Al, N, O, and M,

wherein M ~~denotes at least one rare earth element, preferably at least one~~ is at least one element selected from the group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), La (lanthanum), Gd (gadolinium), Dy (dysprosium), and Nd (neodymium).

90. (Canceled)

91. (Currently Amended) A method according to claim 8 ~~90~~, wherein the gap is in a range of 250-2500 nm.

92. (Original) A method of according to claim 8, wherein each of the first, second and third EL layers comprises an organic material.

93. (Original) A method of according to claim 8, wherein the ink jet method uses a piezo element.

94. (Original) A method according to claim 8, wherein the insulating layer comprises the insulating film for preventing transmission of alkali metals on an insulating film including an organic resin material.

95. (Original) A method according to claim 8, wherein the insulating film for preventing transmission of alkali metals comprises at least one element selected from the group consisting of B (boron), C (carbon), and N (nitrogen), Al (aluminum), Si (silicon), and P (phosphorous).

96. (Currently Amended) A method according to claim 8, wherein the insulating film for preventing transmission of alkali metals comprises Si, Al, N, O, and M,

wherein M ~~denotes at least one rare earth element, preferably at least one~~ is at least one element selected from the group consisting of Ce (cerium), Yb (ytterbium), Sm (samarium), Er (erbium), Y (yttrium), La (lanthanum), Gd (gadolinium), Dy (dysprosium), and Nd (neodymium).